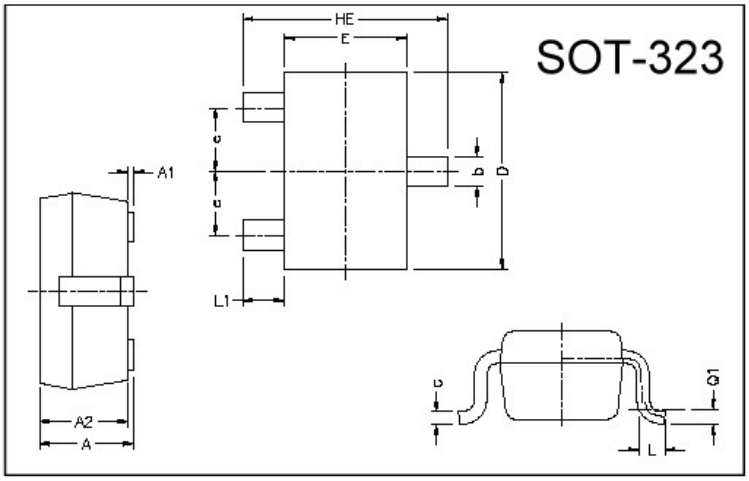
GS411SD

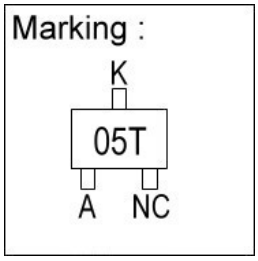
SURFACE MOUNT, SCHOTTKY BARRIER DIODE
VOLTAGE 40V, CURRENT 0.5A

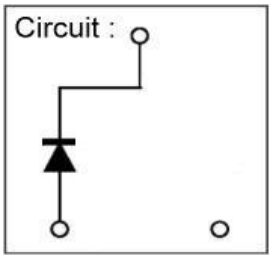
Description

The GS411SD is designed for low power rectification.

Package Dimensions







REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.80	1.10	L1	0.42 REF.	
A1	0	0.10	L	0.15	0.35
A2	0.80	1.00	b	0.25	0.40
D	1.80	2.20	c	0.10	0.25
E	1.15	1.35	e	0.65 REF.	
HE	1.80	2.40	Q1	0.15 BSC.	

Absolute Maximum Ratings at T_A = 25℃

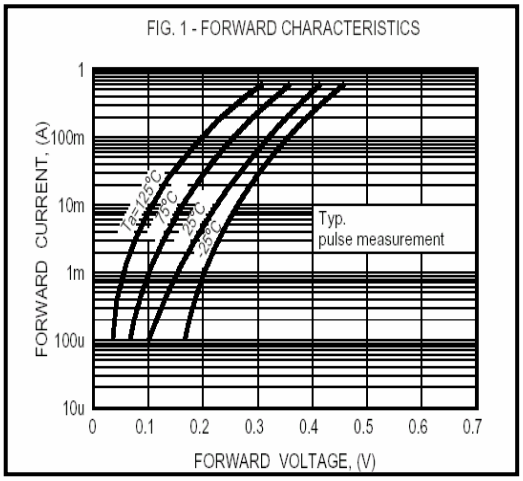
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+125	℃
Storage Temperature	Tstg	-40 ~ +125	℃
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	40	V
Maximum RMS Voltage	V_{RMS}	28	V
Maximum DC Blocking Voltage	V_{DC}	20	V
Peak Forward Surge Current at 8.3mSec single half sine-wave	I_{FSM}	3.0	A
Typical Junction Capacitance between Terminal (Note 1)	C_J	20	pF
Maximum Average Forward Rectified Current	Io	0.5	A
Total Power Dissipation	PD	225	mW

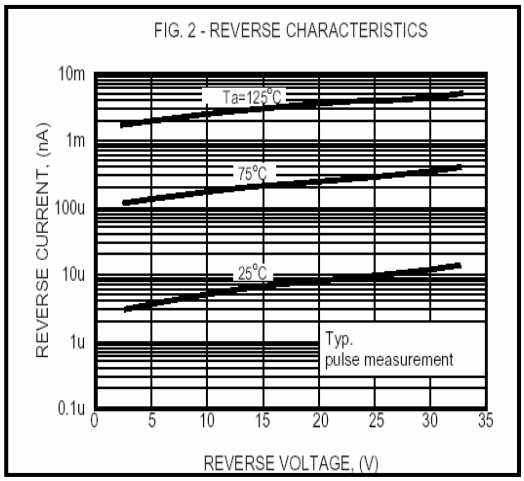
Electrical Characteristics (at T_A = 25℃ unless otherwise noted)

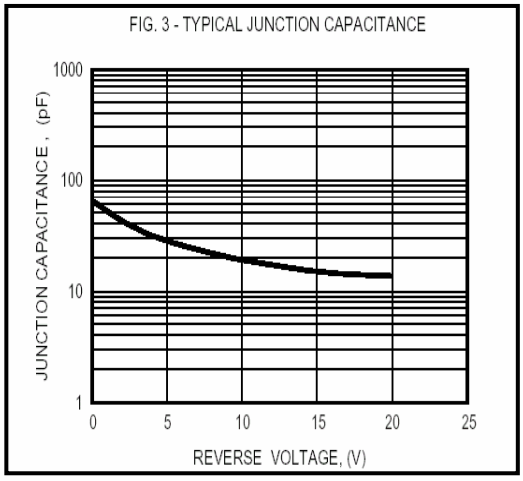
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	$V_{(BR)R}$	40	-	-	V	IR=100μA
Maximum Instantaneous Forward Voltage	V_F	-	-	300	mV	IF1=10mA
		-	-	500		IF2=500mA
Maximum Average Reverse Current	I_R	-	-	30	uA	VR=10V

Notes: 1. Measured at 1.0 MHz and applied reverse voltage of 10 volts.
2. ESD sensitive product handling required.

Characteristics Curve







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